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June 2013

FDMC8360L

N-Channel Shielded Gate Power Trench[®] MOSFET 40 V, 80 A, 2.1 m Ω

Features

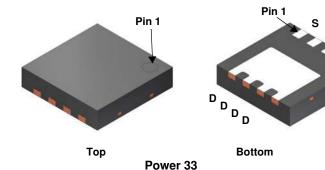
- Shielded Gate MOSFET Technology
- Max $r_{DS(on)} = 2.1 \text{ m}\Omega$ at $V_{GS} = 10 \text{ V}$, $I_D = 27 \text{ A}$
- \blacksquare Max $r_{DS(on)}$ = 3.1 m Ω at V_{GS} = 4.5 V, I_D = 22 A
- High performance technology for extremely low r_{DS(on)}
- Termination is Lead-free
- 100% UIL Tested
- RoHS Compliant

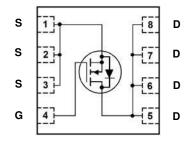
General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that incorporates Shielded Gate technology. This process has been optimized for the on-state resistance and yet maintain superior switching performance.

Application

■ DC-DC Conversion





MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter				Ratings	Units
V_{DS}	Drain to Source Voltage			40	V	
V_{GS}	Gate to Source V	/oltage			±20	V
	Drain Current	-Continuous	T _C = 25 °C		80	
I _D	-Continuous		T _A = 25 °C	(Note 1a)	27	Α
		-Pulsed		(Note 4)	240	
E _{AS}	Single Pulse Ava	lanche Energy		(Note 3)	294	mJ
D	Power Dissipatio	n	T _C = 25 °C		54	w
P_{D}	Power Dissipatio	n	T _A = 25 °C	(Note 1a)	2.3	VV
T _J , T _{STG}	Operating and St	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Note 1)	2.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	53	C/VV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC8360L	FDMC8360L	Power33	13 "	12 mm	3000 units

Electrical Characteristics $T_J = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	acteristics					
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	40			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, referenced to 25 °C		22		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 32 V, V _{GS} = 0 V			1	μΑ
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA

On Characteristics

V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	1.0	1.6	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250 \mu A$, referenced to 25 °C		-6		mV/°C
		$V_{GS} = 10 \text{ V}, I_D = 27 \text{ A}$		1.6	2.1	
r _{DS(on)}	r _{DS(on)} Static Drain to Source On Resistance	$V_{GS} = 4.5 \text{ V}, I_D = 22 \text{ A}$		2.3	3.1	mΩ
		$V_{GS} = 10 \text{ V}, I_D = 27 \text{ A}, T_J = 125 \text{ °C}$		2.2	2.9	
9 _{FS}	Forward Transconductance	$V_{DD} = 5 \text{ V}, \ I_{D} = 27 \text{ A}$		138		S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 00 V V 0 V		4140	5795	pF
C _{oss}	Output Capacitance	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1 \text{ MHz}$		1230	1725	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 101112		36	60	pF
R_g	Gate Resistance		0.1	0.9	2.7	Ω

Switching Characteristics

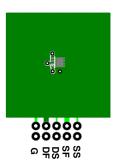
$t_{d(on)}$	Turn-On Delay Time		15	28	ns
t _r	Rise Time	V _{DD} = 20 V, I _D = 27 A,	6.7	14	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$	38	60	ns
t _f	Fall Time		5.3	11	ns
$Q_{g(TOT)}$	Total Gate Charge	V _{GS} = 0 V to 10 V	57	80	nC
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0 \text{ V to } 4.5 \text{ V}$ $V_{DD} = 20 \text{ V},$	26	37	nC
Q_{gs}	Gate to Source Charge	I _D = 27 A	11		nC
Q_{gd}	Gate to Drain "Miller" Charge		5.7		nC

Drain-Source Diode Characteristics

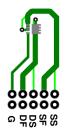
V _{SD} Source to Drain Diod	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 27 \text{ A}$ (Note 2))	8.0	1.3	V
	Source to Drain Diode 1 of ward voltage	$V_{GS} = 0 \text{ V}, I_S = 1.9 \text{ A}$ (Note 2)		0.7	1.2	V
t _{rr}	Reverse Recovery Time	I _E = 27 A, di/dt = 100 A/μs		49	80	ns
Q _{rr}	Reverse Recovery Charge	IF = 27 A, αι/αι = 100 A/μS		29	46	nC

Notes

R_{θ,JA} is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R_{θ,JC} is guaranteed by design while R_{θ,CA} is determined by the user's board design.



a. 53 °C/W when mounted on a 1 in² pad of 2 oz copper



b. 125 °C/W when mounted on a minimum pad of 2 oz copper

- 2. Pulse Test: Pulse Width < 300 $\mu\text{s},$ Duty cycle < 2.0%.
- 3. E_{AS} of 294 mJ is based on starting $T_{J} = 25$ °C, L = 3 mH, $I_{AS} = 14$ A, $V_{DD} = 40$ V, $V_{GS} = 10$ V. 100% test at L = 0.1 mH, $I_{AS} = 44$ A.
- 4. Pulsed Id limited by junction temperature, td<=100 μ S, please refer to SOA curve for more details.

Typical Characteristics T_{.1} = 25 °C unless otherwise noted

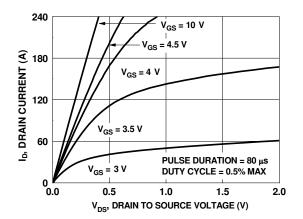


Figure 1. On-Region Characteristics

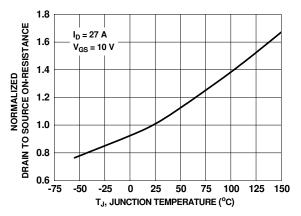


Figure 3. Normalized On-Resistance vs Junction Temperature

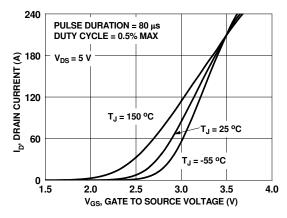


Figure 5. Transfer Characteristics

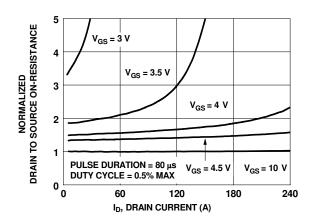


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

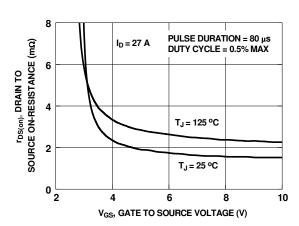


Figure 4. On-Resistance vs Gate to Source Voltage

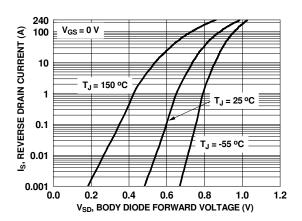


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25$ °C unless otherwise noted

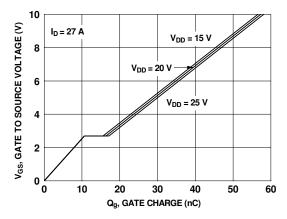


Figure 7. Gate Charge Characteristics

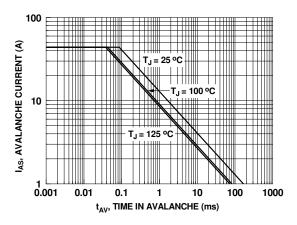


Figure 9. Unclamped Inductive Switching Capability

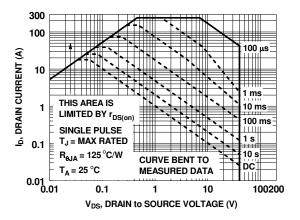


Figure 11. Forward Bias Safe Operating Area

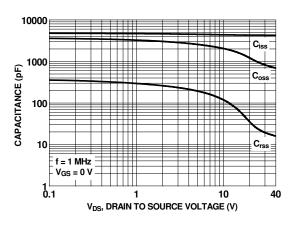


Figure 8. Capacitance vs Drain to Source Voltage

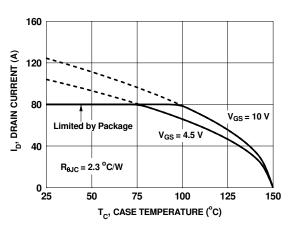


Figure 10. Maximum Continuous Drain Current vs Case Temperature

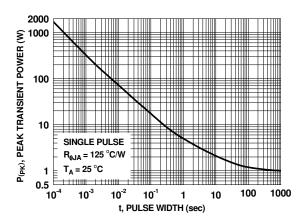


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25 °C unless otherwise noted

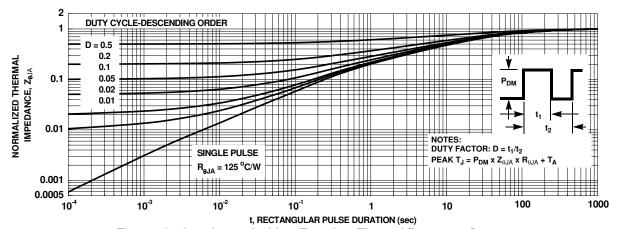
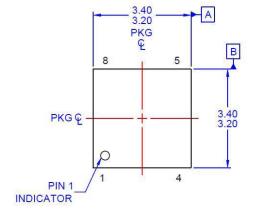
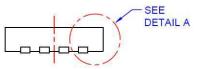
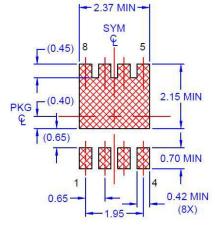


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

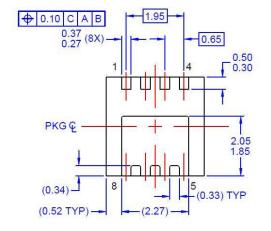
Dimensional Outline and Pad Layout

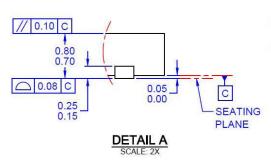






LAND PATTERN RECOMMENDATION





NOTES: UNLESS OTHERWISE SPECIFIED

- A) PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. BA, DATED OCTOBER 2002.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
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